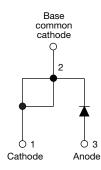


Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A



TO-247AC modified



PRODUCT SUMMARY								
Package	TO-247AC modified (2 pins)							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	1.7 V							
t _{rr} typ.	19 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA15PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15PB60 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	15						
Single pulse forward current	I _{FSM}		150	А					
Maximum repetitive forward current	I _{FRM}		60						
Maximum power dissipation	р	T _C = 25 °C	74	W					
Maximum power dissipation	P _D	T _C = 100 °C	29	٧V					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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RoHS

COMPLIANT

HALOGEN

FREE

to



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ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS						
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage		I _F = 15 A		-	1.3	1.7	V		
	V _{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0			
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6			
Maximum reverse	1	$V_R = V_R$ rated	See fig. 2	-	1.0	10			
leakage current	I_{RM} $T_J = 125 \ ^\circ C, V_R = 0.8 \ x \ V_R \ rated$ See fig. 2		See lig. 2	-	400	1000	μA		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	25	50	pF		
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	12	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CON	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	19	-			
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	42	60	ns		
000 hg. 0, 10	t _{rr2}	T _J = 125 °C		-	74	120			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	- A nC - A/μs		
	I _{RRM2}	T _J = 125 °C	I _F = 15 A	-	6.5	10			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dI _F /dt = 200 A/µs V _B = 200 V	-	80	180			
See fig. 7	Q _{rr2}	T _J = 125 °C	v _R = 200 v	-	220	600			
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-			

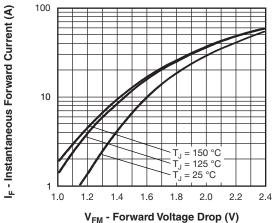
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	- 0.25	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-							
Waight			-	6.0	-	g				
Weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified (JEDEC)		HFA1	5PB60					

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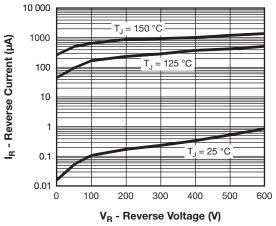
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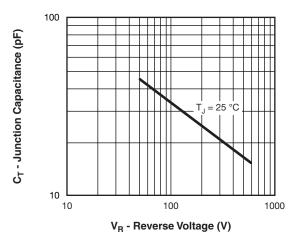
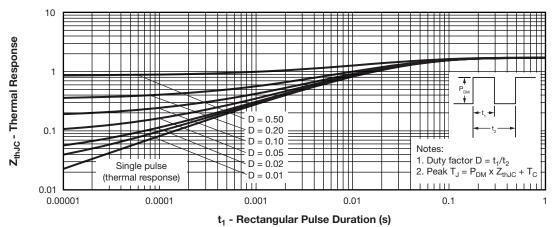
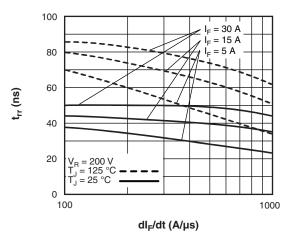


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage









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Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

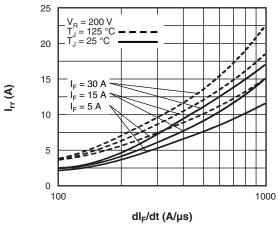


Fig. 6 - Typical Recovery Current vs. dl_F/dt

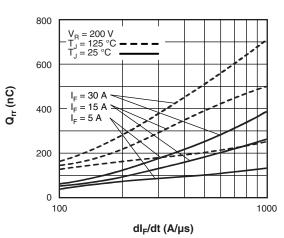


Fig. 7 - Typical Stored Charge vs. dl_F/dt

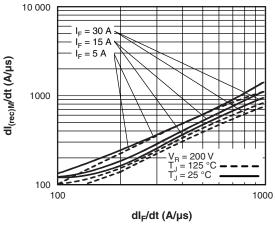


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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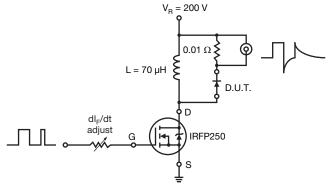
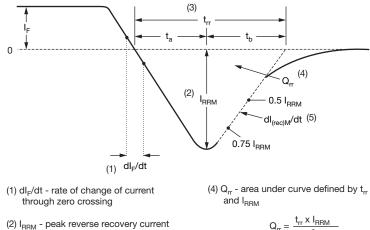


Fig. 9 - Reverse Recovery Parameter Test Circuit



$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(3) $t_{\rm rr}$ - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

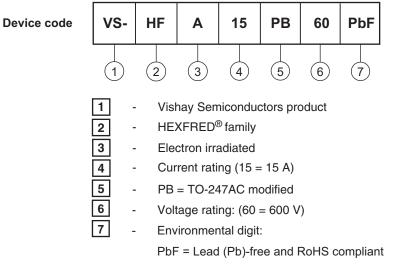
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA15PB60PbF	25	500	Antistatic plastic tube						
VS-HFA15PB60-N3	25	500	Antistatic plastic tube						

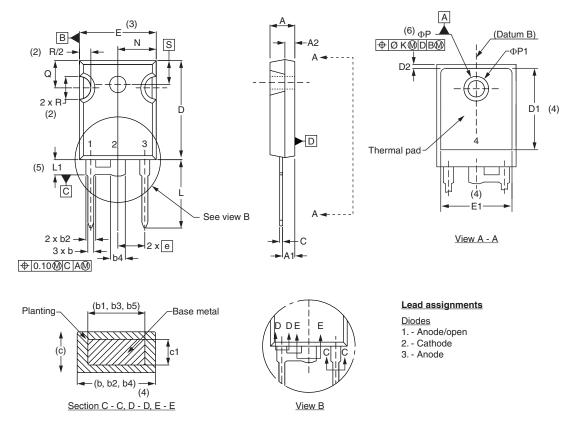
LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95253						
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95225						
	TO-247AC modified -N3	www.vishay.com/doc?95442						

Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ΦK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0.3		
b5	2.59	3.38	0.102	0.133			ΦР	3.56	3.66	0.14	0.144	
С	0.38	0.86	0.015	0.034			Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1

(6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

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